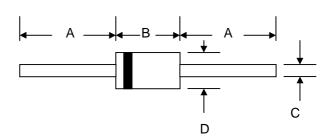


1N5817 - 1N5819

1.0A SCHOTTKY BARRIER RECTIFIER

Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



Mechanical Data

Case: Molded Plastic

Terminals: Plated Leads Solderable per

MIL-STD-202, Method 208

Polarity: Cathode Band

Weight: 0.34 grams (approx.)

Mounting Position: Any

Marking: Type Number

DO-41						
Dim	Min	Max				
Α	25.4	_				
В	4.06	5.21				
С	0.71	0.864				
D	2.00	2.72				
All Dimensions in mm						

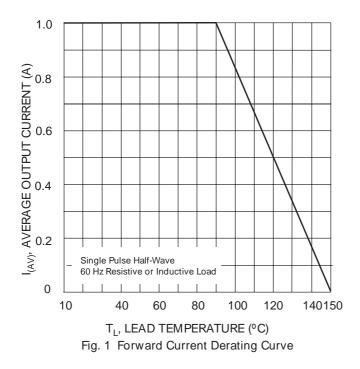
Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

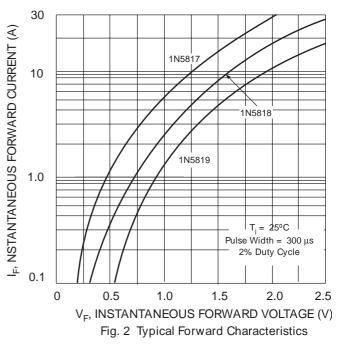
Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

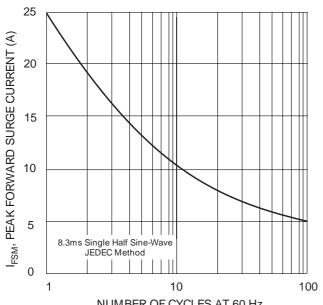
Characteristic		Symbol	1N5817	1N5818	1N5819	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		VRRM VRWM VR	20	30	40	V
RMS Reverse Voltage		VR(RMS)	14	21	28	V
Average Rectified Output Current (Note 1) $@T_L = 90^{\circ}C$		lo	1.0			А
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)		IFSM	25			А
Forward Voltage	@I _F = 1.0A @I _F = 3.0A	VFM	0.450 0.750	0.550 0.875	0.60 0.90	V
Peak Reverse Current At Rated DC Blocking Voltage	@T _A = 25°C @T _A = 100°C	IRM	1.0 10			mA
Typical Junction Capacitance (Note 2)		Cj	110			pF
Typical Thermal Resistance Junction to Lead (Note 1)		$R_{ heta}_{JL}$	60			K/W
Operating and Storage Temperature Range		Тj, Тsтg	-65 to +150			°C

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.









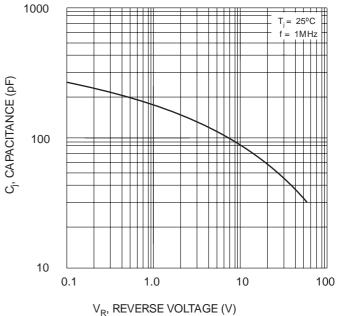


Fig. 4 Typical Junction Capacitance